

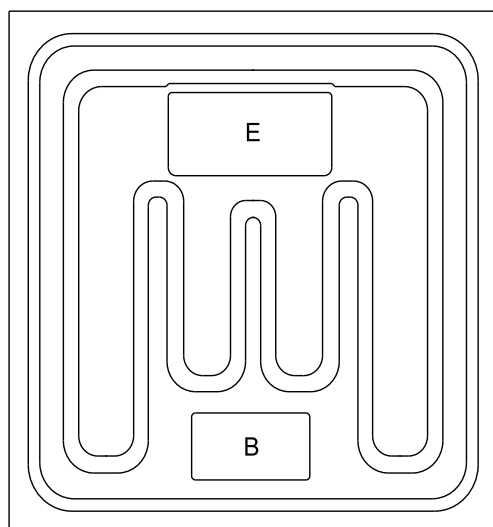
**PROCESS CP312**  
**Power Transistor**  
NPN - Amp/Switch Transistor Chip



**PROCESS DETAILS**

|                          |                    |
|--------------------------|--------------------|
| Process                  | EPITAXIAL PLANAR   |
| Die Size                 | 70 x 70 MILS       |
| Die Thickness            | 9.0 MILS           |
| Base Bonding Pad Area    | 11.4 x 18.1 MILS   |
| Emitter Bonding Pad Area | 13.8 x 23.6 MILS   |
| Top Side Metalization    | Al - 30,000Å       |
| Back Side Metalization   | Ti/Ni/Ag - 11,300Å |

**GEOMETRY**



BACKSIDE COLLECTOR

R1

**GROSS DIE PER 4 INCH WAFER**  
2,230

**PRINCIPAL DEVICE TYPES**  
CZT3120

R4 (22-March 2010)

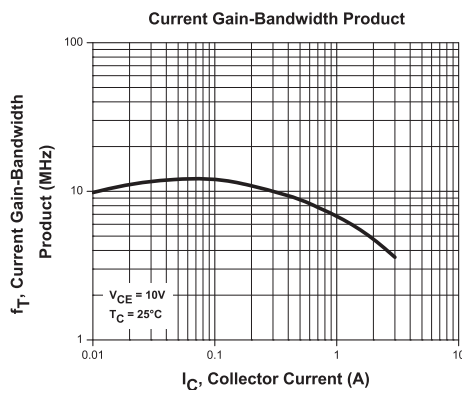
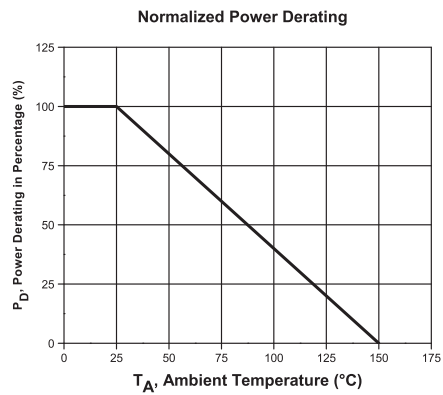
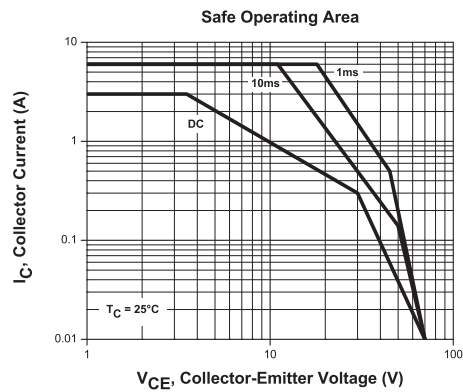
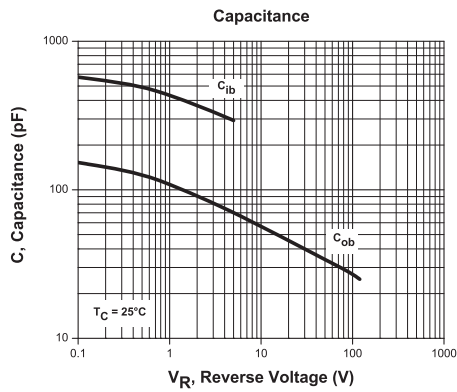
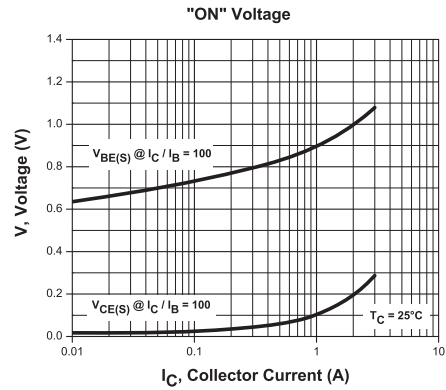
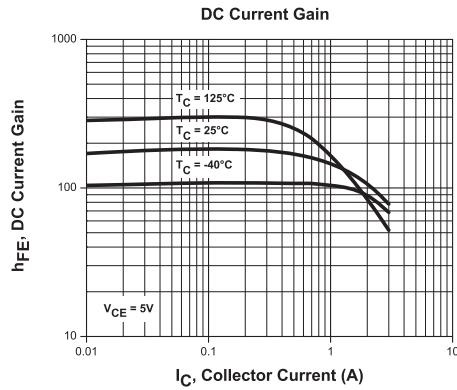
[www.centrasemi.com](http://www.centrasemi.com)

[www.DataSheet4U.com](http://www.DataSheet4U.com)

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# PROCESS CP312

## Typical Electrical Characteristics



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